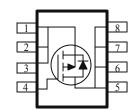
P-Channel 30-V (D-S) MOSFET

These miniature surface mount MOSFETs utilize a high cell density trench process to provide low $r_{DS(on)}$ and to ensure minimal power loss and heat dissipation. Typical applications are DC-DC converters and power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

PRODUCT SUMMARY					
V _{DS} (V)	$r_{DS(on)} m(\Omega)$	I _D (A)			
-30	$13 @ V_{GS} = -10V$	-11.5			
	$19 @ V_{GS} = -4.5V$	-9.3			

- Low r_{DS(on)} provides higher efficiency and extends battery life
- Low thermal impedance copper leadframe SOIC-8 saves board space
- Fast switching speed
- High performance trench technology





ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C UNLESS OTHERWISE NOTED)							
Paramete r	Symbol	Maximum	Units				
Drain-Source Voltage	$ m V_{DS}$	-30	V				
Gate-Source Voltage	V_{GS}	±25	V				
Continuous Drain Current ^a	$T_A=25^{\circ}C$	I.	-11.5				
Continuous Drain Current	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	П	-9.3	A			
Pulsed Drain Current ^b	I_{DM}	±50					
Continuous Source Current (Diode Conduction) ^a	I_S	-2.1	A				
D a	$T_A=25^{\circ}C$	D_	3.1	W			
Power Dissipation ^a	$T_{A}=25^{\circ}C$ $T_{A}=70^{\circ}C$	Гр	2.3				
Operating Junction and Storage Temperature Range	T_{J}, T_{stg}	-55 to 150	°C				

THERMAL RESISTANCE RATINGS						
Parameter	Symbol	Maximum	Units			
Maximum Junction-to-Case ^a	t <= 5 sec	$R_{ heta JC}$	25	°C/W		
Maximum Junction-to-Ambient ^a	t <= 5 sec	$R_{ heta JA}$	50	°C/W		

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

SPECIFICATIONS (T _A = 25°C UNLESS OTHERWISE NOTED)							
Parameter	Cumbal	•	Limits			11554	
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
Static							
Drain-Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0 \text{ V}, I_{D} = -250 \text{ uA}$	-30			V	
Gate-Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250 \text{ uA}$	-1			'	
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 25 \text{ V}$			±100	nA	
Zana Cata Valtana Duain Constant	1	$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}$			-1	uA	
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = -24 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 55^{\circ}\text{C}$			-5		
On-State Drain Current ^A	I _{D(on)}	$V_{DS} = -5 \text{ V}, V_{GS} = -10 \text{ V}$	-50			Α	
Danie Course On BraintenanA	r	V _{GS} = -10 V, I _D = -11.5 A			13		
Drain-Source On-Resistance ^A	r _{DS(on)}	$V_{GS} = -4.5 \text{ V}, I_D = -9.3 \text{ A}$			19.0	mΩ	
Forward Tranconductance ^A	9 _{fs}	$V_{DS} = -15 \text{ V}, I_{D} = -11.5 \text{ A}$		29		S	
Diode Forward Voltage	V_{SD}	$I_S = 2.5 \text{ A}, V_{GS} = 0 \text{ V}$		-0.8		٧	
Dynamic ^b							
Total Gate Charge	Q_g	$V_{DS} = -15 \text{ V}, V_{GS} = -5 \text{ V},$ $I_{D} = -11.5 \text{ A}$		25		nC	
Gate-Source Charge	Q_{gs}			11			
Gate-Drain Charge	Q_{gd}			17			
Input Capacitance	C _{iss}	V _{DS} =-15V, V _{GS} =0V, f=1MHz		2300		pF	
Output Capacitance	C _{oss}			600			
Reverse Transfer Capacitance	C_{rss}			300			
Turn-On Delay Time	t _{d(on)}			15			
Rise Time	t _r	$V_{DD} = -15 \text{ V}, R_L = 6 \Omega,$ ID = -1 A, VGEN = -10 V		13			
Turn-Off Delay Time	$t_{d(off)}$			100		nS	
Fall-Time	t _f			54			

Notes

- a. Pulse test: $PW \le 300us duty cycle \le 2\%$.
- b. Guaranteed by design, not subject to production testing.

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Typical Electrical Characteristics (P-Channel)

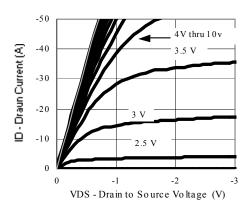


Figure 1. On-Region Characteristics

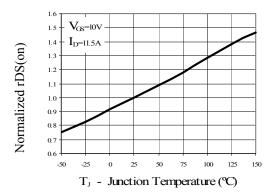


Figure 3. On-Resistance Variation with Temperature

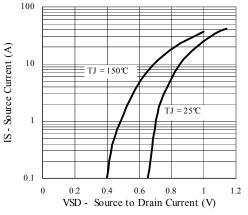


Figure 5. Transfer Characteristics

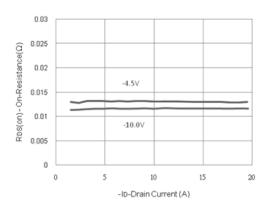


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage

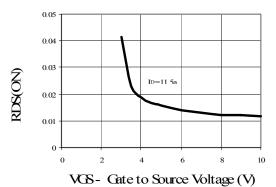


Figure 4. On-Resistance with Gate to Source Voltage

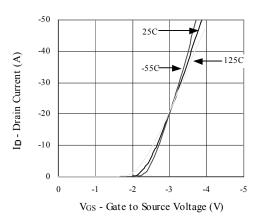


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature

Typical Electrical Characteristics (P-Channel)

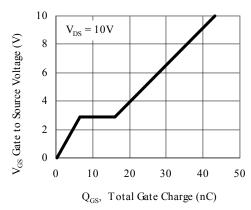


Figure 7. Gate Charge Characteristics

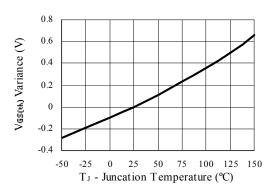


Figure 9. Maximum Safe Operating Area

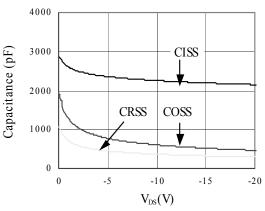


Figure 8. Capacitance Characteristics

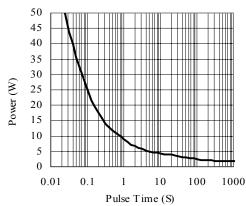


Figure 10. Single Pulse Maximum Power Dissipation

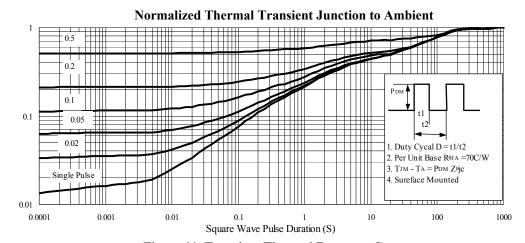
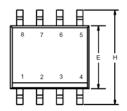
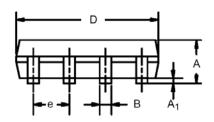


Figure 11. Transient Thermal Response Curve

Package Information

SO-8: 8LEAD





	MILLIN	IETERS	INCHES		
Dim	Min	Max	Min	Max	
Α	1.35	1.75	0.053	0.069	
A ₁	0.10	0.20	0.004	0.008	
В	0.35	0.51	0.014	0.020	
С	0.19	0.25	0.0075	0.010	
D	4.80	5.00	0.189	0.196	
E	3.80	4.00	0.150	0.157	
е	1.27 BSC		0.050 BSC		
Н	5.80	6.20	0.228	0.244	
h	0.25	0.50	0.010	0.020	
L	0.50	0.93	0.020	0.037	
q	0°	8°	0° 8°		

